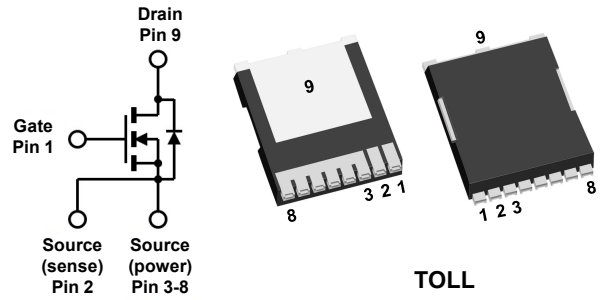


ICEK55NF60T N-Channel Enhancement Mode MOSFET

Product Summary			
I_D	$T_A=25^\circ\text{C}$	55.1A	Max.
$V_{(BR)DSS}$	$I_D=1\text{mA}$	600V	Min.
$r_{DS(on)}$	$V_{GS}=10\text{V}$	32m Ω	Typ.
Q_g	$V_{DS}=400\text{V}$	136nC	Typ.

Features

- TOLL Surface Mount Package
- Low $r_{DS(on)}$
- Ultra Low Gate Charge
- High dv/dt capability
- High Unclamped Inductive Switching (UIS) capability
- High peak current capability
- Increased transconductance performance
- Optimized design for high performance power systems



TOLL

1=Gate, 2=Source(sense)

3-8 =Source (power), 9=Drain



Maximum ratings^a at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current ^b	I_D	$T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$	55.1 34	A
Pulsed drain current ^b	$I_{D, pulse}$	$T_c=25^\circ\text{C}$	200	A
Avalanche energy, single pulse	E_{AS}	$L=10.8\text{mH}$, $V_{DD}=100\text{V}$, $I_{AS}=10.5\text{A}$, $R_G=50\Omega$	595	mJ
Avalanche current, repetitive ^b	I_{AR}	limited by $T_j\text{max}$	10.5	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=400\text{V}$	120	V/ns
Reverse diode dv/dt ruggedness			70	
Gate source voltage	V_{GS}	Static	± 20	V
		AC ($f>1\text{Hz}$)	± 30	
Power dissipation	P_{tot}	$T_c=25^\circ\text{C}$	277	W
Operating and storage temperature	T_j, T_{stg}		-55 to +150	$^\circ\text{C}$

^a Preliminary data sheet - Specifications subject to change.

^b limited by $T_{j\text{max}}$

^c when mounted on 1-inch square 2oz copper-clad FR-4

Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	

Thermal characteristics

Thermal resistance, junction-case	R_{thJC}		-	-	0.45	°C/W
Thermal resistance, junction-ambient °	R_{thJA}	leaded	-	-	45	
Soldering temperature, wave soldering only allowed at leads	T_{sold}	1.6mm (0.063in.) from case for 10 s	-	-	260	°C

Electrical characteristics at $T_j=25^{\circ}\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=1\text{ mA}$	3	4	5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}$	-	-	10	μA
Gate source leakage current	I_{GSS}	$V_{GS}=\pm 30\text{ V}, V_{DS}=0\text{ V}$	-	-	±100	nA
Drain-source on-state resistance	$r_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=25\text{ A}$	-	32	35.5	mΩ
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	4	-	Ω

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=400\text{ V}, f=1\text{ MHz}$	-	3975	-	pF
Reverse transfer capacitance	C_{riss}		-	33	-	
Output capacitance	C_{oss}		-	90	-	
Turn-on delay time	$t_{d(on)}$	$V_{DS}=400\text{ V}, V_{GS}=10\text{ V}, I_D=16\text{ A}, R_G=3\Omega$ (External)	-	105	-	ns
Rise time	t_r		-	42	-	
Turn-off delay time	$t_{d(off)}$		-	120	-	
Fall time	t_f		-	8	-	

Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	

Gate charge characteristics

Gate to source charge	Q_{gs}	$V_{DS}=400V, I_D=16A,$ $V_{GS}=0 \text{ to } 10V$	-	22	-	nC
Gate to drain charge	Q_{gd}		-	71	-	
Gate charge total	Q_g		-	136	-	

Reverse Diode

Continuous forward current	I_S	$V_{GS}=0V$	-	-	55.1	A
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=25A$	-	0.95	-	V
Reverse recovery time	t_{rr}	$V_{RR}=400V, I_S=16A,$ $d_{iF}/d_t=100 \text{ A}/\mu\text{S}$	-	130	-	ns
Reverse recovery charge	Q_{rr}		-	0.8	-	μC
Peak reverse recovery current	I_{rm}		-	11.3	-	A

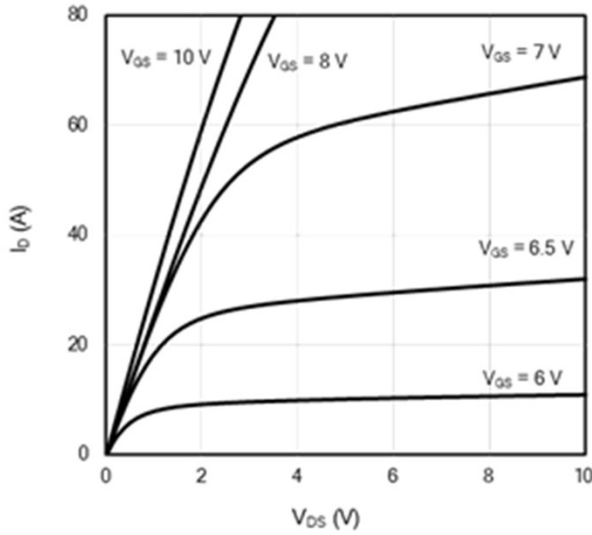


Figure 1: On-Region Characteristics

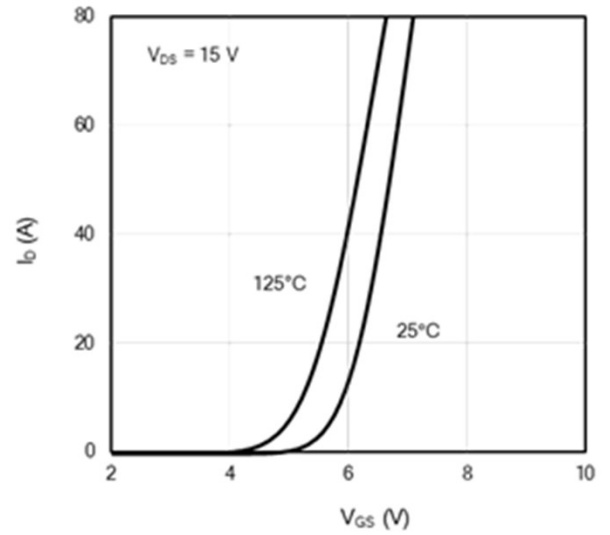


Figure 2: Transfer Characteristics

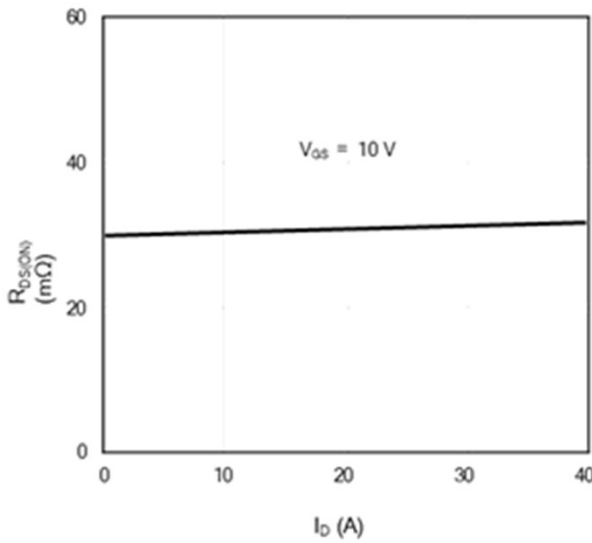


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

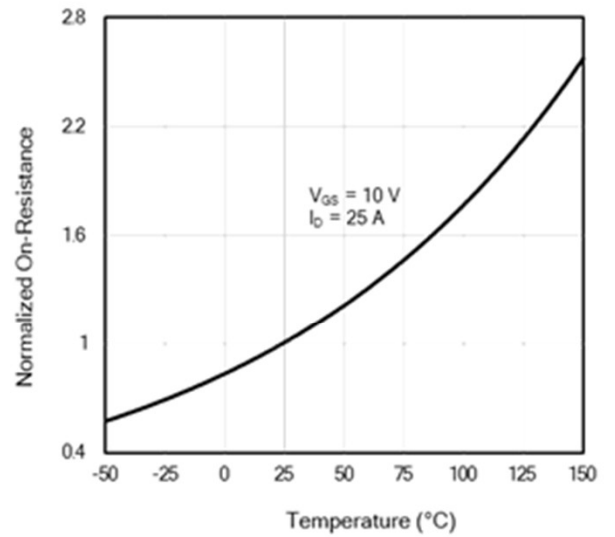


Figure 4: On-Resistance vs. Junction Temperature

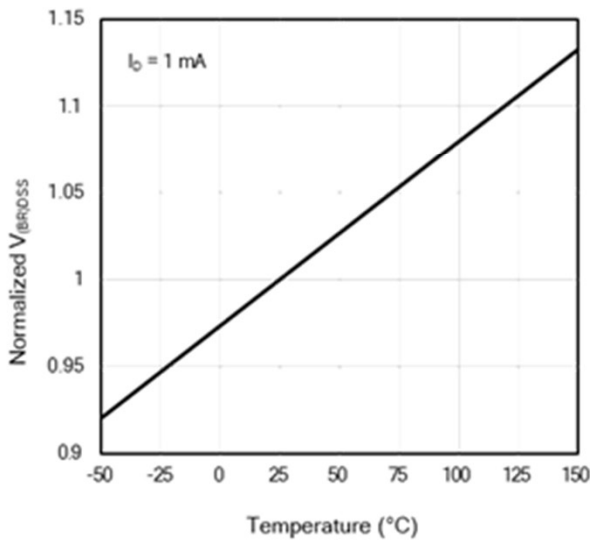


Figure 5: Breakdown Voltage vs. Junction Temperature

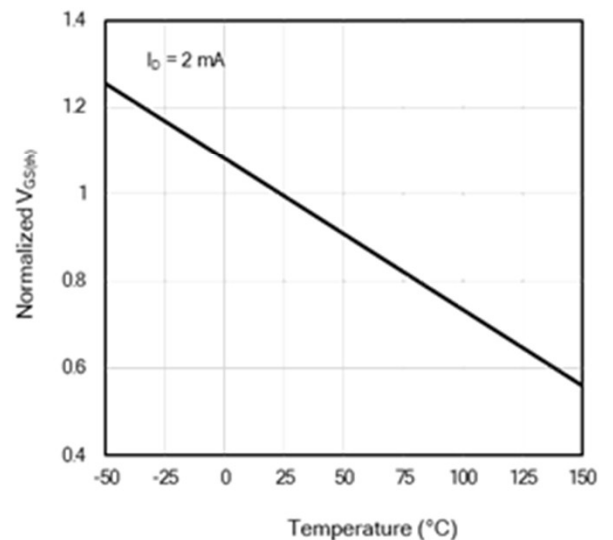


Figure 6: Threshold Voltage vs. Junction Temperature

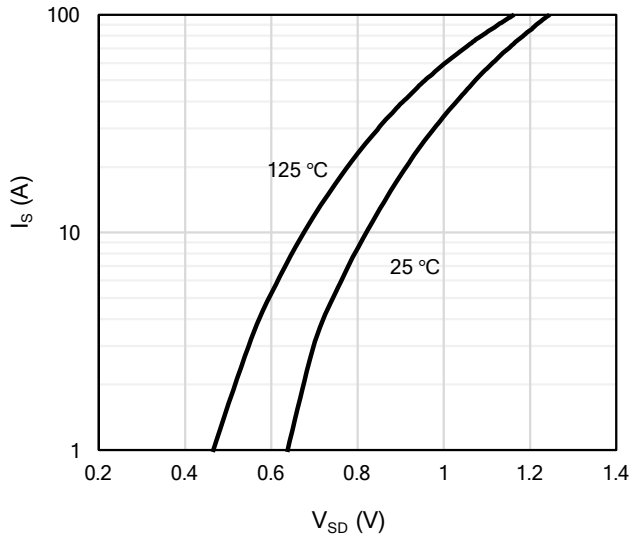


Figure 7: Body-Diode Characteristics

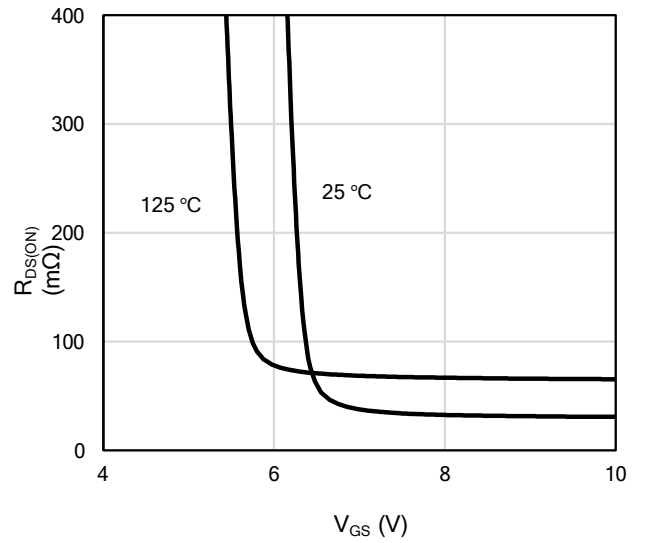


Figure 8: On-Resistance vs. Gate-Source Voltage

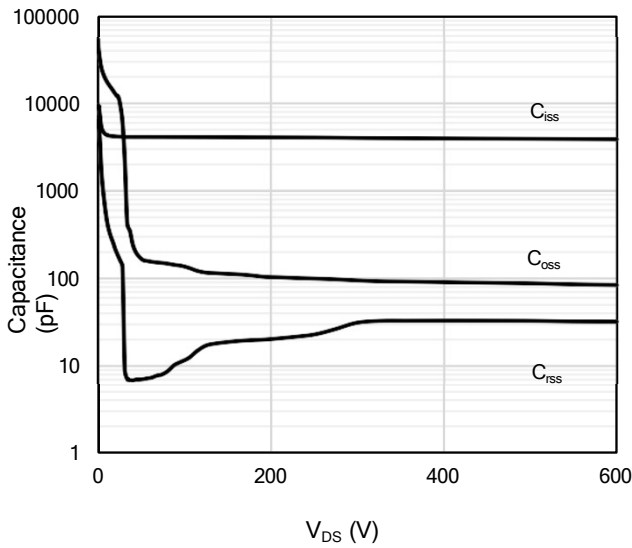


Figure 9: Capacitance Characteristics

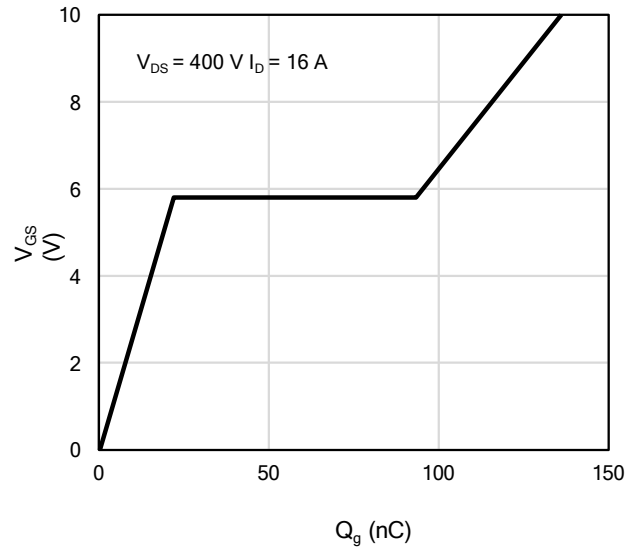


Figure 10: Gate-Charge Characteristics

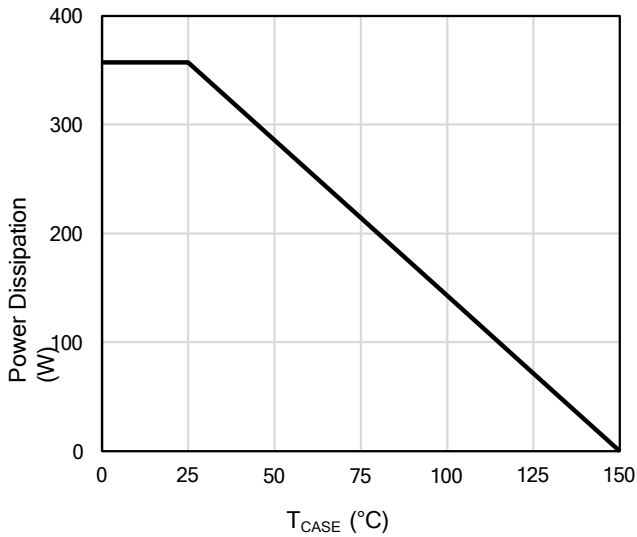


Figure 11: Power De-rating

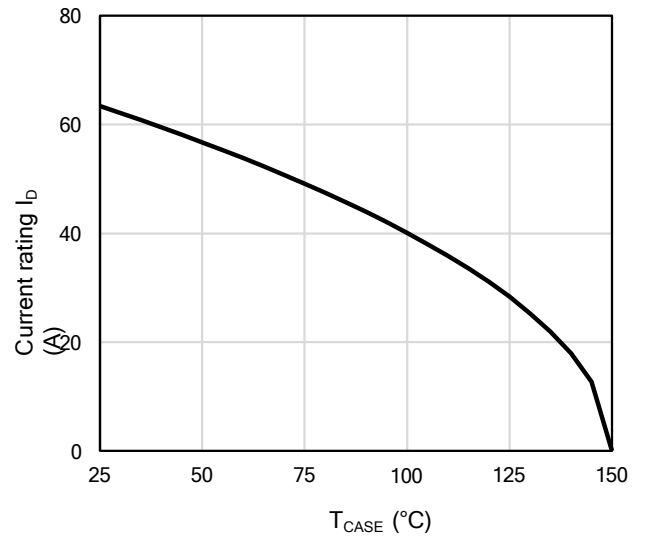


Figure 12: Current De-rating

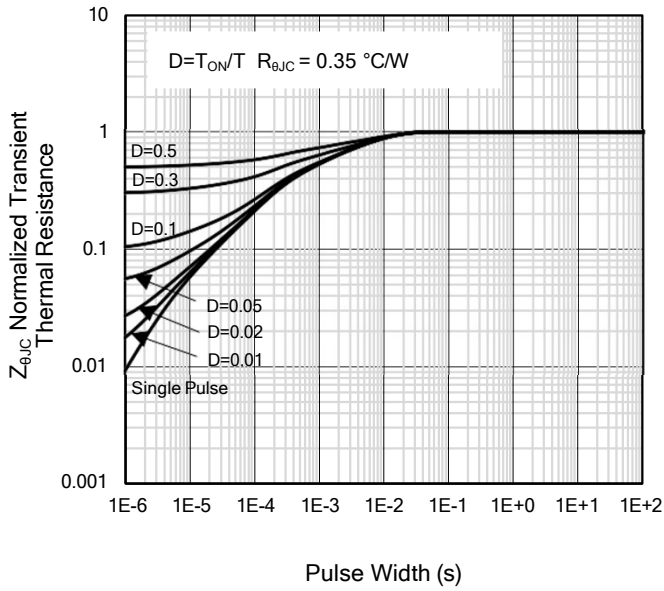


Figure 13: Normalized Maximum Transient Thermal Impedance

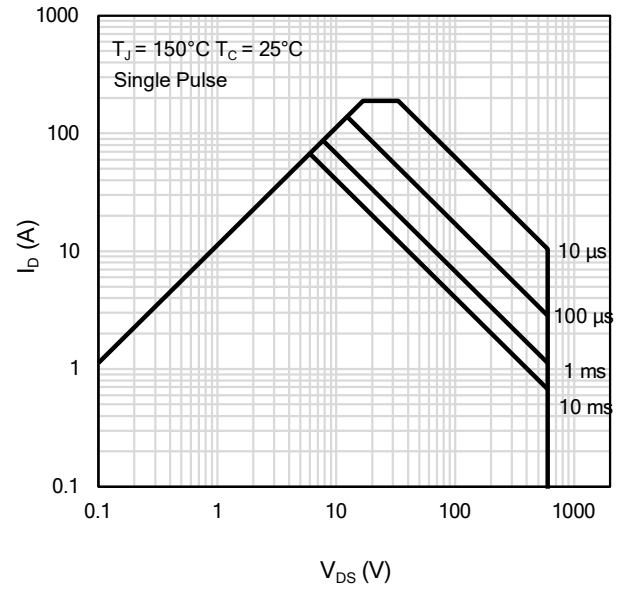
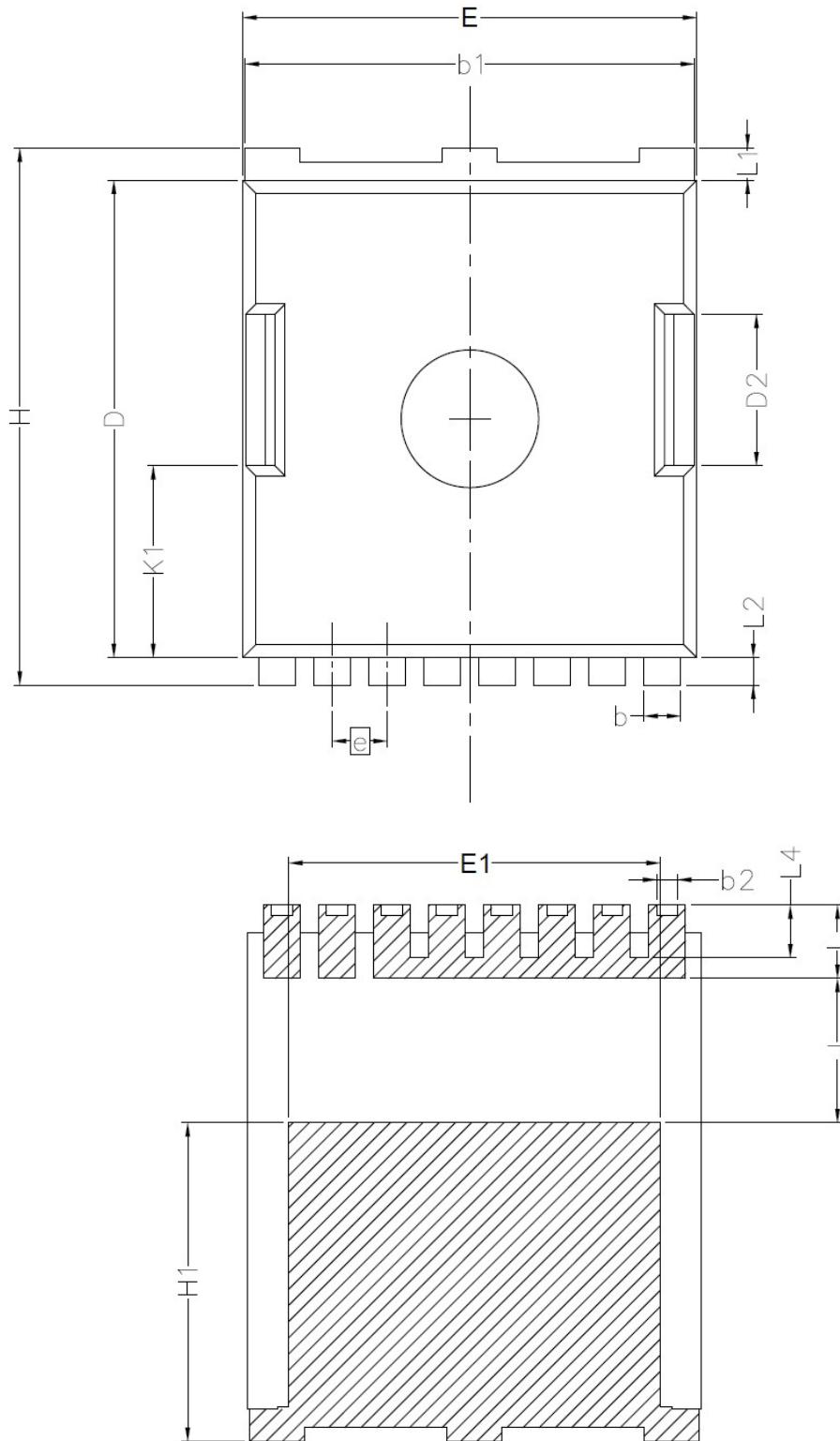
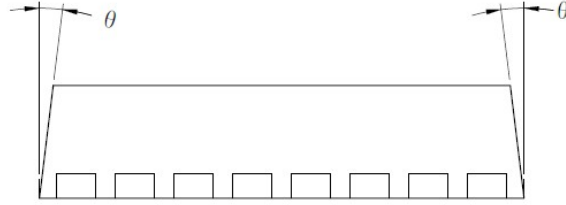
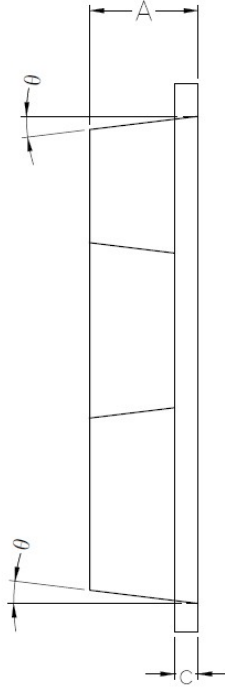


Figure 14: Maximum Forward Biased Safe Operating Area

Package Outline: TOLL



Package Outline: TOLL



Symbol	Min	Nom	Max
A	2.2	2.3	2.4
b	0.7	0.8	0.9
b1	9.7	9.8	9.9
b2	0.42	0.46	0.5
c	0.4	0.5	0.6
D	10.28	10.43	10.58
D2	3.1	3.3	3.5
E	9.7	9.9	10.1
E1	7.9	8.1	8.3
e		1.20 BSC	
H	11.48	11.68	11.88
H1	6.75	6.95	7.15
N		8	
J	3	3.15	3.3
K1	3.98	4.18	4.38
L	1.4	1.6	1.8
L1	0.6	0.7	0.8
L2	0.5	0.6	0.7
L4	1	1.15	1.3
θ	4°	6°	10°

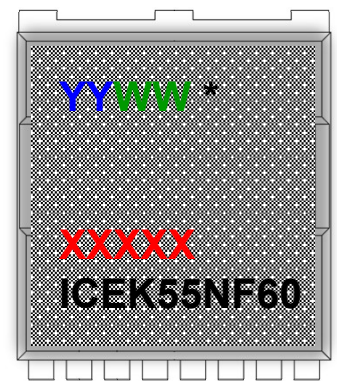
Marking Information

YY = Last two digits of the year

WW = Work week

***** = Site ID

XXXXX = Lot ID



ICEK55NF60 = ICE is Icemos logo and
K55NF60 is a designated device part
number

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